

Supporting Information

Surface plasmon coupling regulated CsPbBr₃ perovskite lasers in metal-insulator-semiconductor structure

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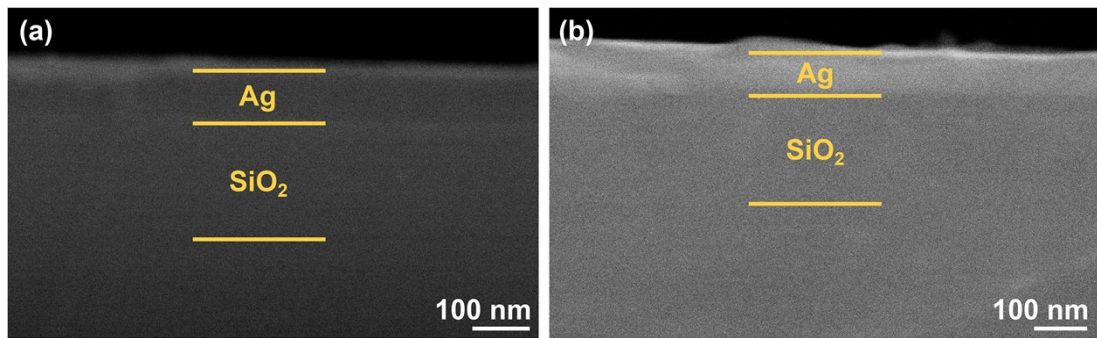


Fig. S1: Cross-sectional FESEM images of samples B (a) and C (b), respectively.

The cross-sectional FESEM images of remaining samples B and C with varying layer thicknesses were shown in Fig. S1. A clear interface distribution can be observed, and the thickness of each layer can match well with our previous designed goal in Table 1. However, due to the measurement condition limitation of FESEM equipment, the upper SiO₂ layers having a thickness of 10 nm and 30 nm are hard to be detected accurately.